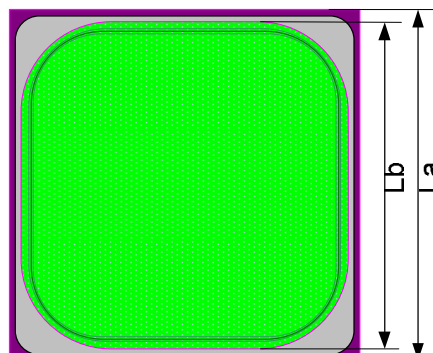


2SF292200HYY

2SF292200HYY FAST RECOVERY DIODE CHIPS

DESCRIPTION

- Ø 2SF292200HYY is a fast recovery diode chips fabricated in silicon epitaxial planar technology;
- Ø Fast recovery times;
- Ø High current capability;
- Ø High surge current capability;
- Ø Low forward voltage drop;
- Ø Low reverse current leakage;
- Ø Top metal is Ag, Back metal is Ag;
- Ø Chip Size: 2920 μ m X 2920 μ m;
- Ø Chip Thickness: 280 $\pm$ 20 μ m;



Chip Topography and Dimensions

La: Chip Size:2920 μ m;

Lb: Pad Size: 2840 μ m;

ORDERING SPECIFICATIONS

Product Name	Specification
2SF292200HYY	For Au and AlSi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	200	V
Average Forward Rectified Current@Tc=150°C	IFAV	20	A
Peak Forward Surge Current@8.3ms	IFSM	390	A
Maximum Operation Junction Temperature	TJ	175	°C
Storage Temperature Range	TSTG	-55~175	°C

ELECTRICAL CHARACTERISTICS (Tamb = 25 °C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	Ir=50 μ A	200	--	V
Forward Voltage	VF1	IF=5A	--	0.84	V
	VF2	IF=20A	--	0.96	V
Reverse Current	IR	VR=200V	--	25	μ A
Reverse recovery time	Trr	IF=0.5A,IR=1A;Irr=0.25A	--	200	ns